

Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-40	V
Collector-Emitter Voltage	V _{CEO}	-40	V
Emitter-Base Voltage	V _{EBO}	-5	V
Collector Current - Continuous	I _C	-1	A
Peak Pulse Collector Current	I _{CM}	-2	A
Peak Base Current	I _{BM}	-1	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation	P _D	400	mW
(Note 5)		500	
Thermal Resistance, Junction to Ambient	R _{θJA}	313	°C/W
(Note 6)		250	
Thermal Resistance, Junction to Leads	R _{θJL}	350	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

- Notes:
5. For a device mounted with collector lead on minimum recommended pad layout 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
 6. Same as Note 5, except the collector lead is on a 25mm x 25mm 1oz copper.
 7. Thermal resistance from junction to solder-point (at the end of the leads).
 8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

Thermal Characteristics and Derating Information

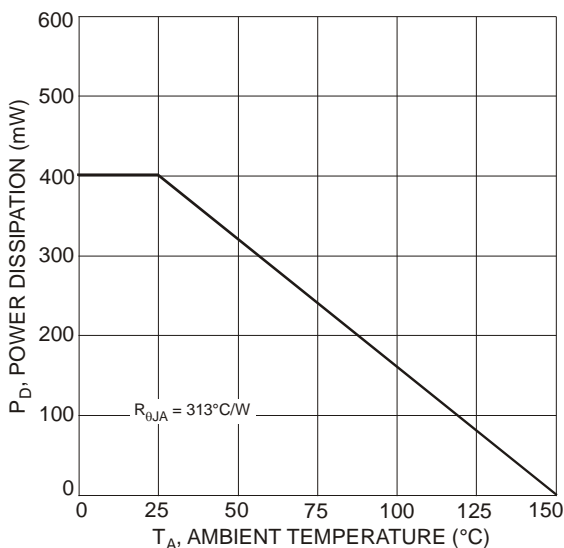


Fig. 1 Power Dissipation vs. Ambient Temperature (Note 3)

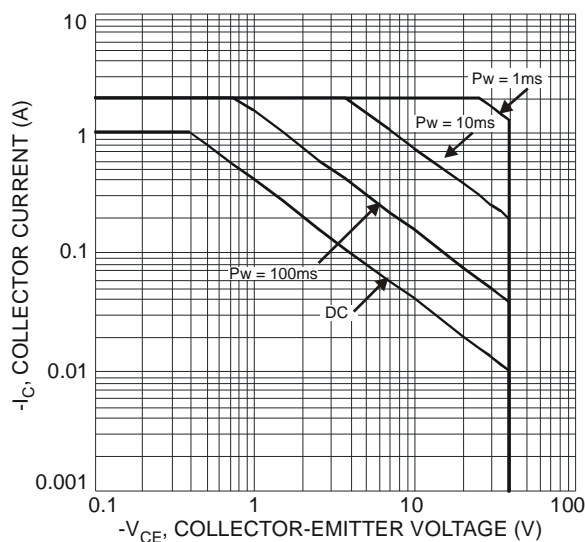


Fig. 2 Typical Collector Current vs. Collector-Emitter Voltage (Note 3)

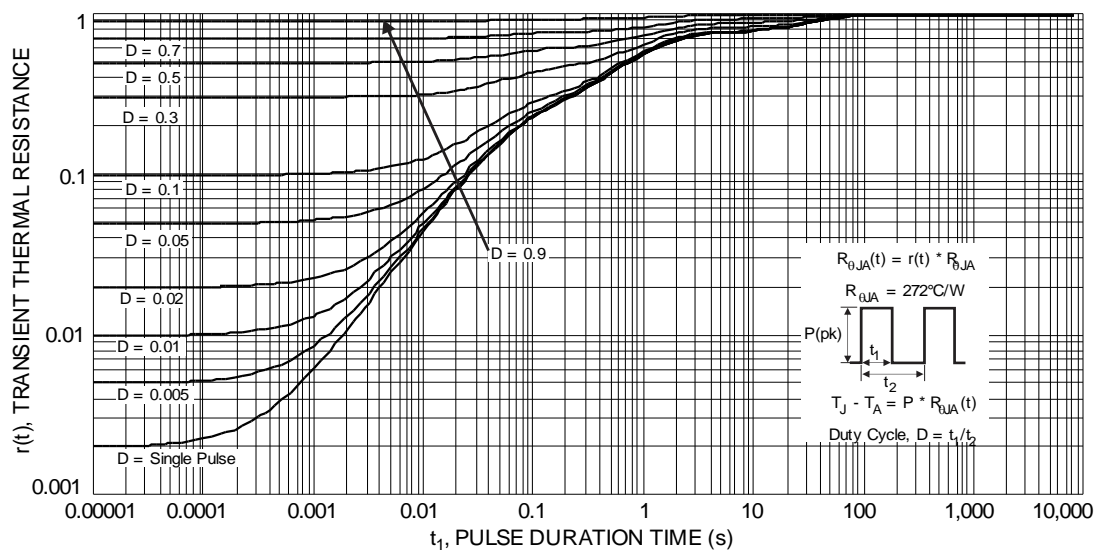


Fig. 3 Transient Thermal Response (Note 3)

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	BV _{CBO}	-40	—	—	V	I _C = -100μA, I _E = 0
Collector-Emitter Breakdown Voltage (Note 9)	BV _{CEO}	-40	—	—	V	I _C = -10mA, I _B = 0
Emitter-Base Breakdown Voltage	BV _{EBO}	-5	—	—	V	I _E = -100μA, I _C = 0
Collector Cutoff Current	I _{CBO}	—	—	-100 -50	nA μA	V _{CB} = -40V, I _E = 0 V _{CB} = -40V, I _E = 0, T _J = +150°C
Collector Cutoff Current	I _{CES}	—	—	-100	nA	V _{CE} = -40V, V _{BE} = 0
Emitter Cutoff Current	I _{EBO}	—	—	-100	nA	V _{EB} = -5V, I _C = 0
ON CHARACTERISTICS (Note 9)						
DC Current Gain	h _{FE}	300 300 250 160	— — — —	— 800 — —	—	V _{CE} = -5V, I _C = -1mA V _{CE} = -5V, I _C = -100mA V _{CE} = -5V, I _C = -500mA V _{CE} = -5V, I _C = 1A
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	— — —	— — —	-200 -250 -500	mV	I _C = -100mA, I _B = -1mA I _C = -500mA, I _B = -50mA I _C = -1A, I _B = -100mA
Collector-Emitter Saturation Resistance	R _{CE(SAT)}	—	—	500	mΩ	I _C = -500mA, I _B = -50mA
Base-Emitter Saturation Voltage	V _{BE(SAT)}	—	—	-1.1	V	I _C = -1A, I _B = -50mA
Base-Emitter Turn On Voltage	V _{BE(ON)}	—	—	-1	V	V _{CE} = -5V, I _C = -1A
SMALL SIGNAL CHARACTERISTICS						
Output Capacitance	C _{obo}	—	13	—	pF	V _{CB} = -10V, f = 1.0MHz
Current Gain-Bandwidth Product	f _T	150	—	—	MHz	V _{CE} = -10V, I _C = -50mA, f = 100MHz
SWITCHING CHARACTERISTICS						
Turn-On Time	t _{on}	—	60	—	ns	V _{CC} = -10V I _C = -0.5A, I _{B1} = -I _{B2} = -25mA
Delay Time	t _d	—	25	—	ns	
Rise Time	t _r	—	35	—	ns	
Turn-Off Time	t _{off}	—	250	—	ns	
Storage Time	t _s	—	220	—	ns	
Fall Time	t _f	—	30	—	ns	

Note: 9. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%.

Typical Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

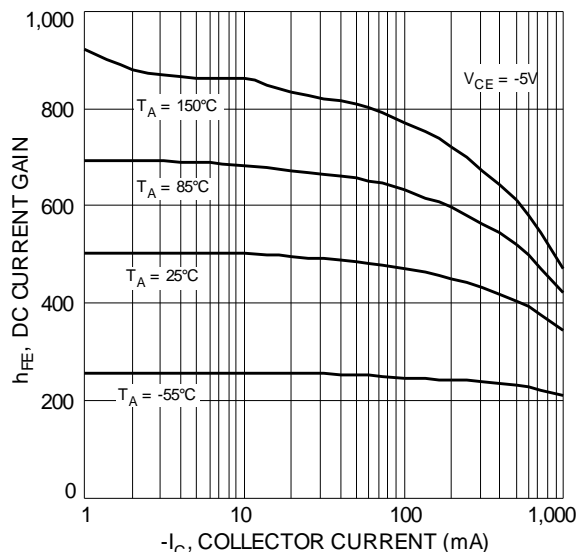


Fig. 4 Typical DC Current Gain vs. Collector Current

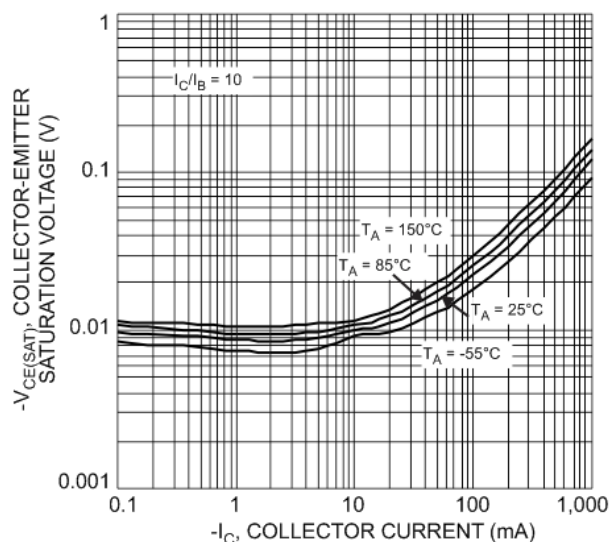


Fig. 5 Typical Collector-Emitter Saturation Voltage vs. Collector Current

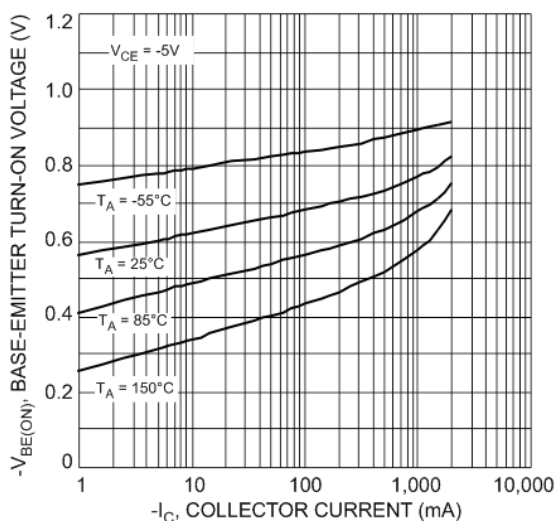


Fig. 6 Typical Base-Emitter Turn-On Voltage vs. Collector Current

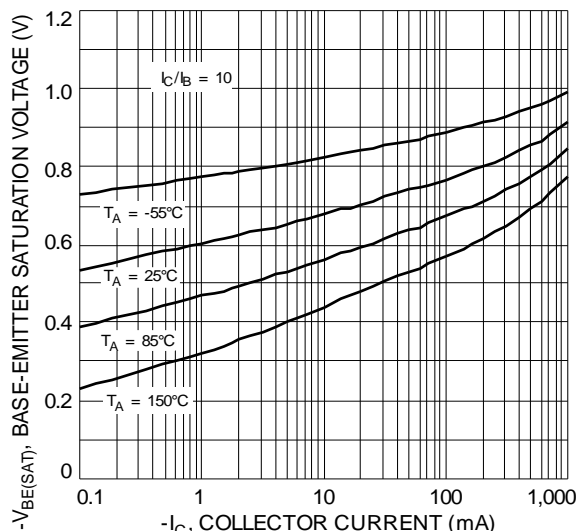


Fig. 7 Typical Base-Emitter Saturation Voltage vs. Collector Current

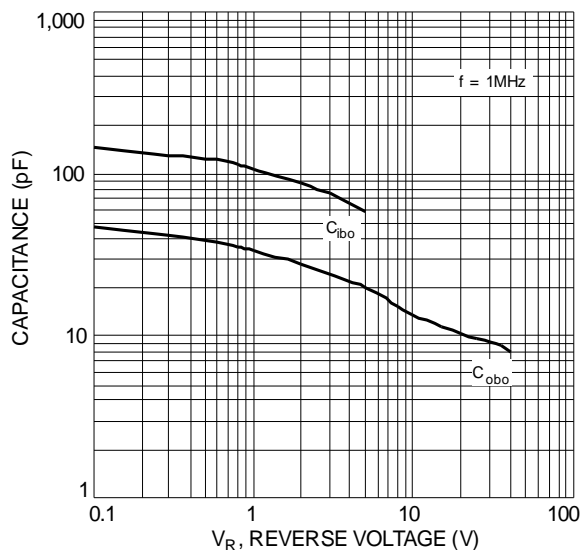
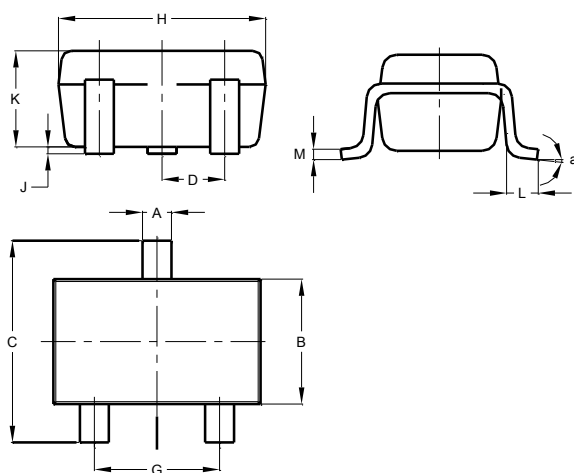


Fig. 8 Typical Capacitance Characteristics

Package Outline Dimensions

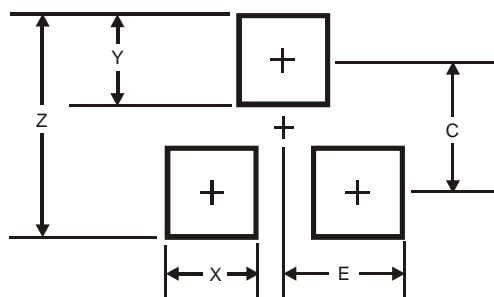
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



SOT323			
Dim	Min	Max	Typ
A	0.25	0.40	0.30
B	1.15	1.35	1.30
C	2.00	2.20	2.10
D	0.650 BSC		
F	0.375	0.475	0.425
G	1.20	1.40	1.30
H	1.80	2.20	2.15
J	0.00	0.10	0.05
K	0.90	1.00	0.95
L	0.25	0.40	0.30
M	0.10	0.18	0.11
a	8°C		
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	SOT323
Z	2.8
X	0.7
Y	0.9
C	1.9
E	1.0

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